

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--|------------------|---------|------------------|
| L2 | 200 | (semiconductor and base and emitter and collector and polysilicon and (dop\$4 impurity) and (concentration dose density)).clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/08/27 09:38 |
| L4 | 200 | (semiconductor and base and emitter and collector and polysilicon and (dop\$4 impurity) and (concentration dose\$3 density)).clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/08/27 09:38 |
| L3 | 960 | 257/197.ccls. | US-PGPUB; USPAT; USOCR | OR | ON | 2007/08/27 08:56 |
| S29 | 408 | (@ad<"20040921" or @rlad<"20040921") and 257/198. ccls. and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/08/27 08:56 |
| L1 | 247 | (semiconductor and base and emitter and polysilicon and (dop\$4 impurity) and (concentration dose density)).clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/08/27 08:47 |
| S23 | 403 | (@ad<"20040921" or @rlad<"20040921") and 257/198. ccls. and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/06/27 15:39 |
| S28 | 225 | (@ad<"20040921" or @rlad<"20040921") and (second with (poly polysilicon) with emitter) and collector and base and bipolar and (carbon germanium argon) not S25 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/27 15:24 |

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| S27 | 1228 | (@ad<"20040921" or @rlad<"20040921") and (second with (poly polysilicon) with emitter) not S25 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/27 15:22 |
| S24 | 14 | (@ad<"20040921" or @rlad<"20040921") and (second near polysilicon near emitter) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/27 14:42 |
| S26 | 7 | ("5818153" "5882976" "6051873" "6194280" "6248650" "6384469").PN. OR ("6686250"). URPN. | US-PGPUB; USPAT; USOCR | OR | ON | 2007/06/27 14:36 |
| S25 | 14 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar base emitter collector sige silicon germanium dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon gallium argon aluminum concentration first second substrate wafer) and (second near polysilicon near emitter) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/27 13:10 |
| S3 | 1258 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/27 13:07 |
| S22 | 19 | (@ad<"20040921" or @rlad<"20040921") and (("4985742" "5010382" "5122845" "5326992" "5378921" "5408120").PN. OR ("5641975"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/01/23 12:59 |

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| S20 | 2 | "6967144" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/23 10:42 |
| S19 | 11 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "sic base" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/23 10:24 |
| S7 | 345 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/23 10:23 |
| S18 | 17 | (@ad<"20040921" or @rlad<"20040921") and (("4583106" "5065209" "5073810" "5117271" "5198375" "5315151" "5321301" "5323032").PN. OR ("5508553"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/01/23 09:07 |

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| S12 | 42 | (@ad<"20040921" or @rlad<"20040921") and (("4319932" "4967254" "5006912" "5063427" "5106767" "5323032" "5346840" "5389803").PN. OR ("5656514"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/01/22 16:18 |
| S9 | 10 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "first base" and "second base" and "first emitter" and "second emitter" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/22 15:50 |
| S4 | 25 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "first base" and "second base" and "first emitter" and "second emitter" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/22 15:49 |
| S2 | 2142 | (@ad<"20040921" or @rlad<"20040921") and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/19 13:45 |

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|----|---|-----------------|---|----|----|------------------|
| S1 | 2 | ("5656514").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/19 09:07 |
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